

DMP2130L

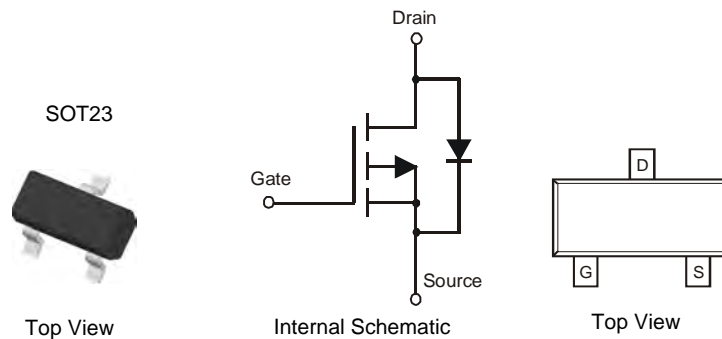
P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low $R_{DS(ON)}$:
 - 75 m Ω @ $V_{GS} = -4.5V$
 - 110 m Ω @ $V_{GS} = -2.7V$
 - 125 m Ω @ $V_{GS} = -2.5V$
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 1, 2 and 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material - Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram Below
- Weight: 0.008 grams (approximate)

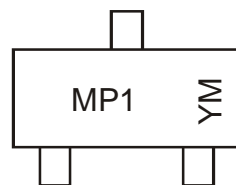


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2130L-7	SOT23	3000/Tape & Reel

- Notes:
1. No purposefully added lead. Halogen and Antimony Free.
 2. Product manufactured with Green Molding Compound and does not contain Halogens or Sb_2O_3 Fire Retardants.

Marking Information



MP1 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: U = 2007)
 M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	2011	2012
Code	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	± 12	V
Drain Current (Note 5) Continuous	I_D	$T_A = 25^\circ\text{C}$	-3.0
		$T_A = 70^\circ\text{C}$	-2.4
Pulsed Drain Current (Note 6)	I_{DM}	-15	A
Body-Diode Continuous Current (Note 5)	I_S	2.0	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	1.4	W
Thermal Resistance, Junction to Ambient (Note 5); Steady-State	$R_{\theta JA}$	90	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	μA	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$
Gate-Body Leakage Current	I_{GSS}	—	—	± 100	nA	$V_{DS} = 0\text{V}, V_{GS} = \pm 12\text{V}$
Gate Threshold Voltage	$V_{GS(th)}$	-0.6	—	-1.25	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
On State Drain Current (Note 7)	$I_{D(ON)}$	-15	—	—	A	$V_{GS} = -4.5\text{V}, V_{DS} = -5\text{V}$
Static Drain-Source On-Resistance (Note 7)	$R_{DS(ON)}$	—	51	75	m Ω	$V_{GS} = -4.5\text{V}, I_D = -3.5\text{A}$
		—	87	110		$V_{GS} = -2.7\text{V}, I_D = -3.0\text{A}$
		—	99	125		$V_{GS} = -2.5\text{V}, I_D = -2.6\text{A}$
Forward Transconductance (Note 7)	g_{FS}	—	7.3	—	S	$V_{DS} = -10\text{V}, I_D = -3.0\text{A}$
Diode Forward Voltage (Note 7)	V_{SD}	—	0.79	-1.26	V	$I_S = -1.7\text{A}, V_{GS} = 0\text{V}$
Maximum Body-Diode Continuous Current (Note 5)	I_S	—	—	1.7	A	—
DYNAMIC PARAMETERS (Note 8)						
Total Gate Charge	Q_g	—	7.3	—	nC	$V_{GS} = -4.5\text{V}, V_{DS} = -10\text{V}, I_D = -3.0\text{A}$
Gate-Source Charge	Q_{gs}	—	2.0	—	nC	$V_{GS} = -4.5\text{V}, V_{DS} = -10\text{V}, I_D = -3.0\text{A}$
Gate-Drain Charge	Q_{gd}	—	1.9	—	nC	$V_{GS} = -4.5\text{V}, V_{DS} = -10\text{V}, I_D = -3.0\text{A}$
Turn-On Delay Time	$t_{D(on)}$	—	12	—	ns	$V_{DS} = -10\text{V}, V_{GS} = -4.5\text{V},$ $R_L = 10\Omega, R_G = 6\Omega$
Turn-On Rise Time	t_r	—	20	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	38	—	ns	
Turn-Off Fall Time	t_f	—	41	—	ns	
Input Capacitance	C_{iss}	—	443	—	pF	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	128	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	101	—	pF	

- Notes:
- Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width $t \leq 10\text{s}$.
 - Repetitive Rating, pulse width limited by junction temperature.
 - Test pulse width $t = 300\mu\text{s}$.
 - Guaranteed by design. Not subject to production testing.